- Single Chip With Easy Interface Between **UART and Serial-Port Connector of an External Modem or Other Computer** Peripheral
- Five Drivers and Three Receivers Meet or **Exceed the Requirements of TIA/EIA-232-F** and ITU Recommendation V.28
- Designed to Support Data Rates up to 120 kbit/s
- ESD Protection Meets Or Exceeds 10 kV on RS-232 Pins and 5 kV on All Other Pins (Human-Body Model)
- **Complement to the SN75185**
- Pin-to-Pin Replacement for the Goldstar GD75323
- **Functional Replacement for the MC145405**

DW OR N PACKAGE (TOP VIEW) Vcc [20 🛮 V_{DD} 19 1DY 1DA **1** 2 2DA **∏** 3 18 2DY 3DA **∏** 4 17 1 3DY 1RY Π 5 16**∏** 1RA 2RY Γ 6 15 1 2RA 4DA **∏** 7 14 1 4DY 3RY **[**] 8 13**∏** 3RA 12 5DY 5DA [] 9 GND **1** 10 11 [] V_{SS}

description

The SN75196 combines five drivers and three receivers from the trade-standard SN75188 and SN75189 bipolar quadruple drivers and receivers, respectively. The flow-through design of the SN75196 decreases the part count, reduces the board space required, and allows easy interconnection of the UART and serial-port connector. The all-bipolar circuits and processing of the SN75196 provide a rugged, low-cost solution for this function.

The SN75196 complies with the requirements of TIA/EIA-232-F and ITU (formerly CCITT) V.28 standards. These standards are for data interchange between a host computer and peripheral at signal rates of up to 20 kbit/s. The switching speeds of the SN75196 are fast enough to support rates of up to 120 kbit/s with lower capacitive loads (shorter cables). Interoperability at the higher signaling rates cannot be assured unless the designer has design control of the cable and the interface circuits at both ends. For interoperability at signaling rates of up to 120 kbit/s, use of TIA/EIA-423-B (ITU V.10) and TIA/EIA-422-B (ITU V.11) standards are recommended.

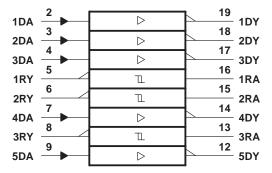
The SN75196 is characterized for operation over a temperature range of 0°C to 70°C.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

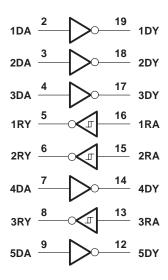


logic symbol†



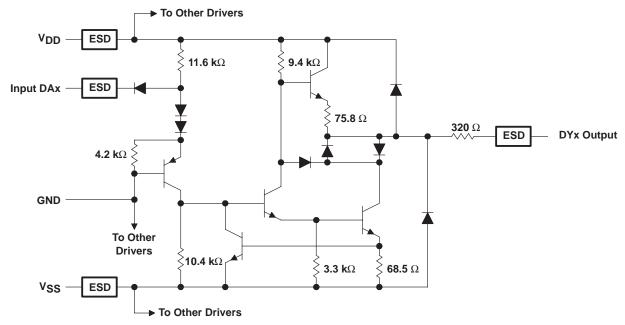
[†] This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



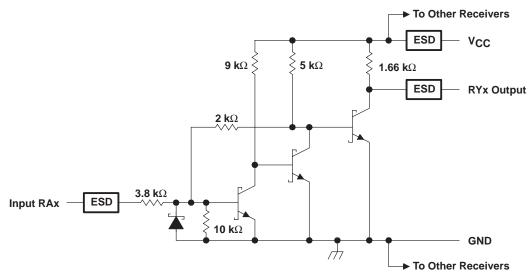


schematic of each driver



Resistor values shown are nominal.

schematic of each receiver



Resistor values shown are nominal.

absolute maximum ratings over operating free-air temperature (unless otherwise noted)†

| Supply voltage, V _{CC} (see Note 1) | 10 V |
|--|------------------------------|
| Supply voltage, V _{DD} (see Note 1) | |
| Supply voltage, V _{SS} (see Note 1) | |
| Input voltage range, V _I : Driver | –15 V to 7 V |
| Receiver | –30 V to 30 V |
| Output voltage range, V _O (Driver) | – 15 V to 15 V |
| Low-level output current, IOL (Receiver) | 20 mA |
| Continuous total power dissipation | See Dissipation Rating Table |
| Electrostatic discharge: DY and RA to GND (see Note 2) | Class 3, A: 10 kV, B: 500 V |
| All pins (see Note 2) | Class 3, A: 5 kV, B: 300 V |
| Storage temperature range, T _{stq} | |
| Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds . | |

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. All voltages are with respect to the network ground terminal.

DISSIPATION RATING TABLE

| PACKAGE | $T_{\mbox{$A$}} \leq 25^{\circ}\mbox{$C$}$ POWER RATING | DERATING FACTOR‡ ABOVE T _A = 25°C | T _A = 70°C POWER RATING |
|---------|---|--|---------------------------------------|
| DW | 1125 mW | 9.0 mW/°C | 720 mW |
| N | 1150 mW | 9.2 mW/°C | 736 mW |

[‡] This is the inverse of the traditional junction-to-case thermal resistance ($R_{\theta JA}$).

recommended operating conditions

| | | MIN | NOM | MAX | UNIT |
|--|----------|------|-----|-------|------|
| Supply voltage, V _{DD} | | 7.5 | 9 | 13.5 | V |
| Supply voltage, V _{SS} | | -7.5 | -9 | -13.5 | V |
| Supply voltage, V _{CC} | | 4.5 | 5 | 5.5 | V |
| High-level input voltage, VIH | Driver | 1.9 | | | V |
| Low-level input voltage, V _{IL} | Driver | | | 0.8 | V |
| High level output ourrent leve | Driver | | | -6 | mA |
| High-level output current, IOH | Receiver | | | -0.5 | mA |
| High level output ourrent lev | Driver | | | 6 | mΛ |
| High-level output current, IOL | Receiver | | | 16 | mA |
| Operating free-air temperature,TA | | 0 | | 70 | °C |



^{2.} Per MIL-PRF-38535, Method 3015.7

supply currents over operating free-air temperature range

| | PARAMETER | | TEST CONDI | TIONS | | MIN | MAX | UNIT |
|-----|-------------------------------------|------------------------|--------------------|-------------------|--------------------------|-----|------|------|
| | | All inputs at 1.9 V, | No load | $V_{DD} = 9 V$, | $V_{SS} = -9 V$ | | 25 | |
| | Supply current from VDD | All lilputs at 1.9 v, | NO load | $V_{DD} = 12 V$, | $V_{SS} = -12 \text{ V}$ | | 32 | mA |
| lDD | Зарріў сапені поні УДД | All inputs at 0.8 V, | No load | $V_{DD} = 9 V$, | $V_{SS} = -9 V$ | | 7.5 | IIIA |
| | | All lilputs at 0.6 v, | No load | $V_{DD} = 12 V$, | $V_{SS} = -12 \text{ V}$ | | 9.5 | |
| | | All inputs at 1.9 V, | No load | $V_{DD} = 9 V$, | $V_{SS} = -9 V$ | | -25 | |
| | Supply current from VSS | All lilputs at 1.9 v, | No load | $V_{DD} = 12 V$, | $V_{SS} = -12 \text{ V}$ | | -32 | mA |
| ISS | Supply current from vSS | All inputs at 0.8 V, | No load | $V_{DD} = 9 V$, | $V_{SS} = -9 V$ | | -5.3 | IIIA |
| | | All ilipuis at 0.6 v, | NO IOAU | $V_{DD} = 12 V$, | $V_{SS} = -12 \text{ V}$ | | -5.3 | |
| Icc | Supply current from V _{CC} | V _{CC} = 5 V, | All inputs at 5 V, | No load | | | 20 | mA |

DRIVER SECTION

electrical characteristics over operating free-air temperature range, V_{DD} = 9 V, V_{SS} = -9 V, V_{CC} = 5 V, (unless otherwise noted)

| | PARAMETER | | TEST CONDIT | TIONS | MIN | TYP | MAX | UNIT |
|-----------------|--|-------------------------------------|---------------------|--------------------------------------|------|------|-------|------|
| Vон | High-level output voltage | $V_{IL} = 0.8 V$, | $R_L = 3 k\Omega$, | See Figure 1 | 6 | 7.5 | | V |
| VOL | Low-level output voltage (see Note 3) | V _{IH} = 1.9 V, | $R_L = 3 k\Omega$, | See Figure 1 | | -7.5 | -6 | V |
| lн | High-level input current | $V_1 = 5 V$, | See Figure 2 | | | | 10 | μΑ |
| I _{IL} | Low-level input current | $V_{I} = 0$, | See Figure 2 | | | | -1.6 | mA |
| IOS(H) | High-level short-circuit output current (see Note 4) | V _{IL} = 0.8 V, | V _O = 0, | See Figure 1 | -4.5 | -9 | -19.5 | mA |
| IOS(L) | Low-level short-circuit output current (see Note 4) | V _{IH} = 2 V, | V _O = 0, | See Figure 1 | 4.5 | 9 | 19.5 | mA |
| r _o | Output resistance (see Note 5) | V _{CC} = V _{DD} = | $= V_{SS} = 0,$ | $V_0 = -2 \text{ V to } 2 \text{ V}$ | 300 | | | Ω |

- NOTES: 3. The algebraic convention, where the more positive (less negative) limit is designated as maximum, is used in this data sheet for logic levels only, e.g., if –10 V is a maximum, the typical value is a more negative voltage.
 - 4. Output short-circuit conditions must maintain the total power dissipation below absolute maximum ratings.
 - 5. Test conditions are those specified by TIA/EIA-232-F and as listed above.

switching characteristics, V_{DD} = 12 V, V_{SS} = -12 V, V_{CC} = 5 V $\pm 10\%$, T_A = 25°C

| | PARAMETER | | TEST CONDITI | ONS | MIN | TYP | MAX | UNIT |
|------------------|---|--|---------------------------|-------------------------|-----|-----|-----|------|
| tPLH | Propagation delay time, low- to high-level output | $R_L = 3 \text{ k}\Omega \text{ to } 7 \text{ k}\Omega,$ | C _L = 15 pF, | See Figure 3 | | 315 | 500 | ns |
| tPHL | Propagation delay time, high- to low-level output | $R_L = 3 \text{ k}\Omega \text{ to } 7 \text{ k}\Omega,$ | C _L = 15 pF, | See Figure 3 | | 75 | 175 | ns |
| | Transition time, | $R_1 = 3 k\Omega$ to $7 k\Omega$ | C _L = 15 pF, | See Figure 3 | | 60 | 100 | ns |
| tTLH | low- to high-level output (see Note 6) | K[= 3 K22 to 7 K22 | $C_L = 2500 \text{ pF},$ | See Figure 3 and Note 6 | | 1.7 | 2.5 | μs |
| t | Transition time, high- to low-level output | $R_1 = 3 k\Omega$ to $7 k\Omega$ | C _L = 15 pF, | See Figure 3 | | 40 | 75 | ns |
| t _{THL} | (see Note 7) | | C _L = 2500 pF, | See Figure 3 and Note 7 | | 1.5 | 2.5 | μs |

NOTES: 6. Measured between –3-V and 3-V points of the output waveform (TIA/EIA-232-F conditions), all unused inputs are tied either high or low.

7. Measured between 3-V and –3-V points of the output waveform (TIA/EIA-232-F conditions), all unused inputs are tied either high or low.



RECEIVER SECTION

electrical characteristics over recommended operating conditions (unless otherwise noted)

| | PARAMETER | ТІ | EST CONDITION | IS | MIN | TYP [†] | MAX | UNIT |
|-------------------|---|-----------------------------|-------------------------------|--------------------------|-------|------------------|------|------|
| \/ | Positive-going input threshold voltage | See Figure 5 | T _A = 25°C | | 1.75 | 1.9 | 2.3 | V |
| VIT+ | Positive-going input threshold voltage | See Figure 5 | T _A = 0°C to 70 °C | | | | 2.3 | V |
| V _{IT} _ | Negative-going input threshold voltage | See Figure 5 | | | 0.75 | 0.97 | 1.25 | V |
| V _{hys} | Input hysteresis (V _{IT+} - V _{IT-}) | See Figure 5 | | | 0.5 | | | V |
| V/011 | High-level output voltage | Jan - 0.5 mA | See Figure 5 | V _{IH} = 0.75 V | 2.6 | 4 | 5 | V |
| VOH | nigri-iever output voitage | $I_{OH} = -0.5 \text{ mA},$ | See Figure 5 | Inputs open | 2.6 | | | V |
| VOL | Low-level input voltage | $I_{OL} = 10 \text{ mA},$ | V _I = 3 V, | See Figure 5 | | 0.2 | 0.45 | V |
| | High-level input current | V _I = 25 V | | | 3.6 | | 8.3 | mΑ |
| ЧН | r ligh-level input current | V _I = 3 V | | | 0.43 | | | IIIA |
| 1 | Low-level input current | V _I = -25 V | | | -3.6 | | -8.3 | mΑ |
| l IIL | Low-level input current | V _I = −3 V | | | -0.43 | | | ША |
| los | Short-circuit output current | See Figure 4 | | | | -3.4 | -12 | mA |

[†] All typical values are at $T_A = 25^{\circ}C$, $V_{CC} = 5$ V, $V_{DD} = 9$ V, and $V_{SS} = -9$ V.

switching characteristics, V_{CC} = 5 V, V_{DD} = 12 V, V_{SS} = -12 V, T_A = 25°C

| | PARAMETER | TE | ST CONDITIO | MIN | TYP | MAX | UNIT | |
|------|---|------------------------|-----------------------------|--------------|-----|-----|------|----|
| tPLH | Propagation delay time, low- to high-level output | $C_L = 50 \text{ pF},$ | $R_L = 5 \text{ k}\Omega$, | See Figure 6 | | 107 | 500 | ns |
| tPHL | Propagation delay time, high- to low-level output | $C_L = 50 \text{ pF},$ | $R_L = 5 \text{ k}\Omega$, | See Figure 6 | | 42 | 150 | ns |
| tTLH | Transition time, low- to high-level output | $C_L = 50 \text{ pF},$ | $R_L = 5 \text{ k}\Omega$, | See Figure 6 | | 175 | 525 | ns |
| tTHL | Transition time, high- to low-level output | $C_L = 50 \text{ pF},$ | $R_L = 5 \text{ k}\Omega$, | See Figure 6 | | 16 | 60 | ns |



PARAMETER MEASUREMENT INFORMATION

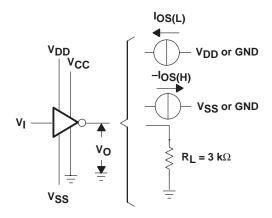


Figure 1. Driver Test Circuit for V_{OH} , V_{OL} , $I_{OS(H)}$, and $I_{OS(L)}$

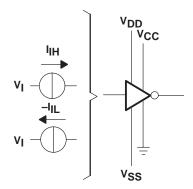
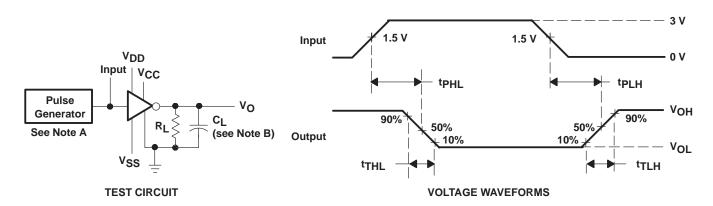


Figure 2. Driver Test Circuit for IIH and IIL



- NOTES: A. The pulse generator has the following characteristics: t_W = 25 μ s, PRR = 20 kHz, Z_O = 50 Ω , t_Γ = t_f < 50 ns.
 - B. C_L includes probe and jig capacitance.

Figure 3. Driver Test Circuit and Voltage Waveforms



PARAMETER MEASUREMENT INFORMATION

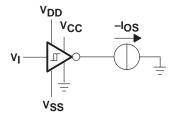


Figure 4. Receiver Test Circuit for IOS

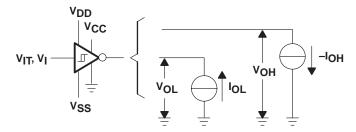
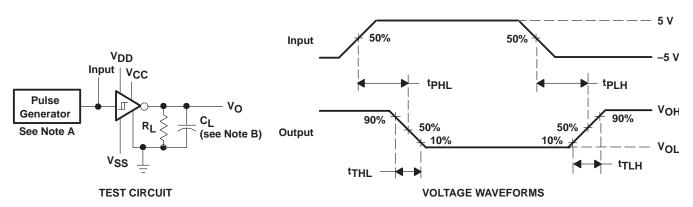


Figure 5. Receiver Test Circuit for V_{IT} , V_{OH} , and V_{OL}



NOTES: A. The pulse generator has the following characteristics: t_W = 25 μ s, PRR = 20 kHz, Z_O = 50 Ω , t_f = t_f < 50 ns.

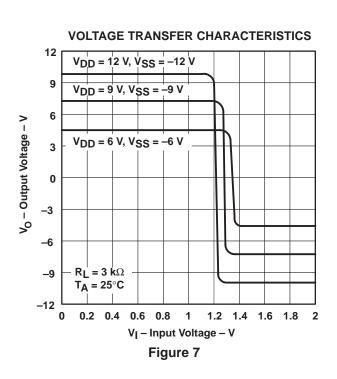
B. C_L includes probe and jig capacitance.

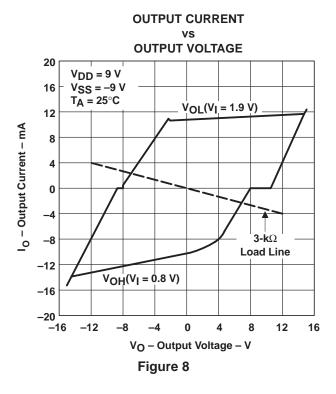
Figure 6. Receiver Propagation and Transition Times

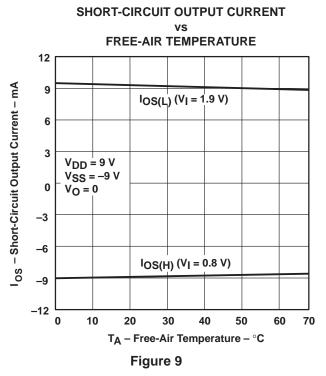


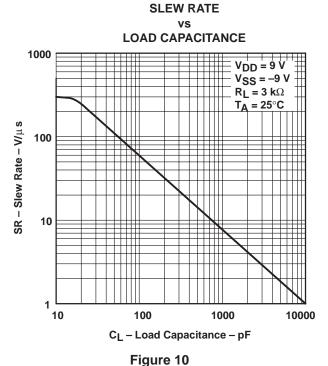
TYPICAL CHARACTERISTICS

DRIVER SECTION

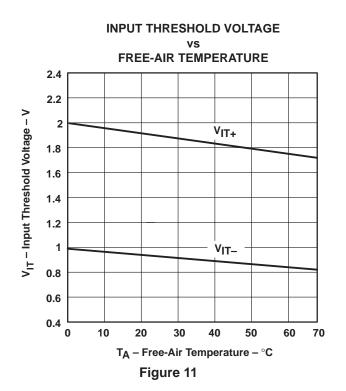


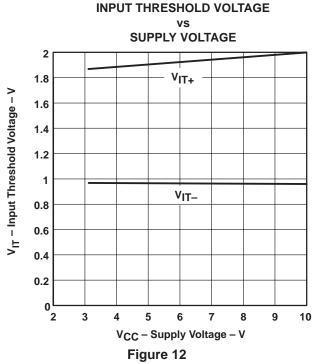




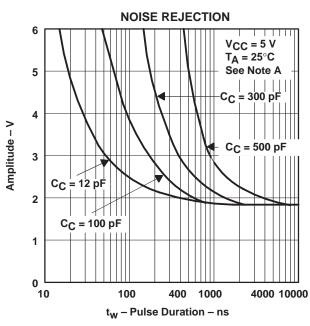


TYPICAL CHARACTERISTICS **RECEIVER SECTION**





MAXIMUM SUPPLY VOLTAGE



FREE-AIR TEMPERATURE 16 14 V_{DD} - Maximum Supply Voltage - V 12 10 8 6 4 2 $R_L \ge 3 \text{ k}\Omega$ (from each output to GND) 0 0 10 20 60 50

NOTE A: This figure shows the maximum amplitude of a positive-going pulse that, starting from 0 V, does not cause a change of the output level.

Figure 14

 T_A – Free-Air Temperature – $^{\circ}C$

70





APPLICATION INFORMATION

Diodes placed in series with the V_{DD} and V_{SS} terminals protect the SN75196 in the fault condition when the device outputs are shorted to V_{DD} or V_{SS} and the power supplies are at low and provide low-impedance paths to ground (see Figure 15).

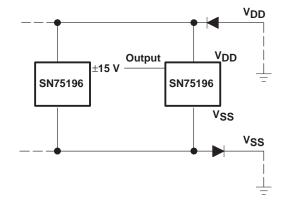
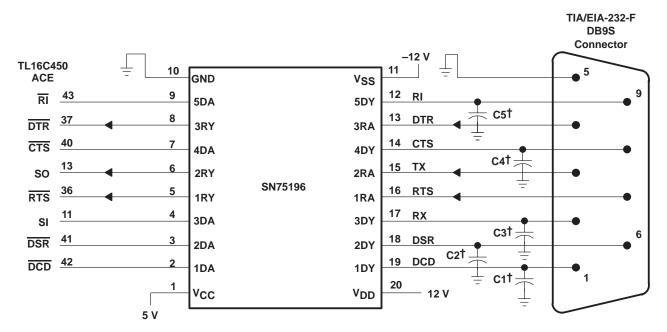


Figure 15. Power-Supply Protection to Meet Power-Off Fault Conditions of TIA/EIA-232-F



[†] See Figure 10 to select the correct values for the loading capacitors (C1, C2, C3, C4, and C5), which may be required to meet the RS-232 maximum slew-rate requirement of 30 V/μs. The value of the loading capacitors required depends upon the line length and desired slew rate, but is typically 330 pF.

NOTE A: To use the receivers only, $V_{\mbox{DD}}$ and $V_{\mbox{SS}}$ must both be powered or tied to ground.

Figure 16. Typical TIA/EIA-232-F Connection



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PACKAGING INFORMATION

| Orderable Device | Status | Package Type | Package Drawing | Pins | Package Qty | Eco Plan | Lead finish/ Ball material | MSL Peak Temp | Op Temp (°C) | Device Marking (4/5) | Samples |
|------------------|--------|--------------|--------------------|------|----------------|--------------|-------------------------------|--------------------|--------------|----------------------|---------|
| | | | | | | | (6) | | | | |
| SN75196DW | NRND | SOIC | DW | 20 | 25 | RoHS & Green | NIPDAU | Level-1-260C-UNLIM | 0 to 70 | SN75196 | |
| SN75196DWR | NRND | SOIC | DW | 20 | 2000 | RoHS & Green | NIPDAU | Level-1-260C-UNLIM | 0 to 70 | SN75196 | |

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





| | Dimension designed to accommodate the component width |
|----|---|
| B0 | Dimension designed to accommodate the component length |
| K0 | Dimension designed to accommodate the component thickness |
| W | Overall width of the carrier tape |
| P1 | Pitch between successive cavity centers |

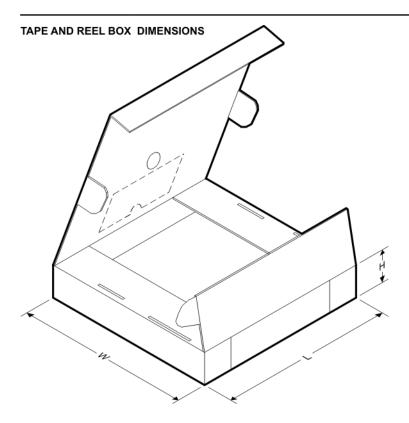
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

| Device | Package Type | Package Drawing | | | Reel Diameter (mm) | Reel Width W1 (mm) | A0 (mm) | B0 (mm) | K0 (mm) | P1 (mm) | W (mm) | Pin1 Quadrant |
|------------|-----------------|--------------------|----|------|--------------------------|--------------------------|------------|------------|------------|------------|-----------|------------------|
| SN75196DWR | SOIC | DW | 20 | 2000 | 330.0 | 24.4 | 10.8 | 13.3 | 2.7 | 12.0 | 24.0 | Q1 |

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*All dimensions are nominal

| I | Device | Package Type | Package Drawing | Pins | SPQ | Length (mm) | Width (mm) | Height (mm) |
|---|------------|--------------|-----------------|------|------|-------------|------------|-------------|
| I | SN75196DWR | SOIC | DW | 20 | 2000 | 367.0 | 367.0 | 45.0 |

PACKAGE MATERIALS INFORMATION

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TUBE



*All dimensions are nominal

| Device | Package Name | Package Type | Pins | SPQ | L (mm) | W (mm) | T (µm) | B (mm) |
|-----------|--------------|--------------|------|-----|--------|--------|--------|--------|
| SN75196DW | DW | SOIC | 20 | 25 | 507 | 12.83 | 5080 | 6.6 |
| SN75196DW | DW | SOIC | 20 | 25 | 506.98 | 12.7 | 4826 | 6.6 |



SOIC



NOTES:

- 1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.43 mm per side.
- 5. Reference JEDEC registration MS-013.



SOIC



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOIC



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



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